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(P-L12)	Low-Pressure Hybrid Chemical Vapor Deposition for Efficient Perovskite Solar Cells and Module M. -H. Li, P. -S. Shen, J. -S. Chen, Y. -H. Chiang, P. Chen, T. -F. Guo, <i>Nat'l Cheng Kung Univ., Taiwan</i>	256

Friday, July 8

Special Session : New Driving Technologies (9 : 15 ~ 10 : 25)

Chairpersons :	R. Hattori, <i>Kyushu Univ., Japan</i> M. Mitani, <i>Sharp Corp., Japan</i>
9:15 (SP-1)	In-Cell Capacitive Touch Panel Structures and Their Readout Circuits (Invited) S. -H. Lee, J. -S. An, S. -K. Hong, O. -K. Kwon, <i>Hanyang Univ., Korea</i> 258
9:40 (SP-2)	High-Definition In-Cell Touch Panel with Parallel Scanning Method (Invited) K. Tada, K. Kida, S. Yamagishi, T. Maruyama, J. Mugiraneza, Y. Sugita, H. Kawamori, T. Saitoh, H. Shioe, <i>Sharp Corp., Japan</i> 262
10:05 (SP-3)	Blue-Phase Pixel Circuit Design to Enlarge Operation Voltage and Combine Polarity Inversion with a-IGZO Thin-Film-Transistors C. -E. Wu, C. -L. Lin, M. -X. Wang, <i>Nat'l Cheng Kung Univ., Taiwan</i> 266

— Coffee Break —

Session 4 : High-Performance TFTs (10 : 40 ~ 11 : 50)

Chairpersons :	M. -H. Yoon, <i>Gwangju Inst. of Sci. and Technol., Korea</i> S. Horita, <i>JAIST, Japan</i>
10:40 (4-1)	Understanding of Carrier Transport in High-Performance Solid Phase Crystallized Poly-Si Nano-Wire Transistors (Invited) M. Oda, K. Sakuma, Y. Kamimuta, M. Saitoh, <i>Toshiba Corp., Japan</i> 270
11:05 (4-2)	Radio Frequency Electronics in a-IGZO TFT Technology (Invited) K. Ishida ¹ , T. Meister ¹ , R. Shabaniour ¹ , B. K. Boroujeni ¹ , C. Carta ¹ , G. Cantarella ² , L. Petti ² , N. Münzenrieder ^{2,3} , G. A. Salvatore ² , G. Tröster ² , F. Ellinger ¹ , ¹ <i>Technische Universität Dresden,</i> <i>Germany</i> , ² <i>Swiss Federal Inst. of Technol., Switzerland</i> , ³ <i>Univ. of Sussex, United Kingdom</i> 273
11:30 (4-3)	Ultrahigh-Performance Poly-Si Thin Film Transistor Using Multi-Line Beam Continuous-Wave Laser Lateral Crystallization T. T. Nguyen, M. Hiraiwa, T. Hirata, S. Kuroki, <i>Hiroshima Univ., Japan</i> 277

— Lunch —

Session 5 : Perovskite Photovoltaics (13 : 00 ~ 13 : 40)

Chairpersons :	C. Li, <i>Kochi Univ. of Technol., Japan</i> T. Miyadera, <i>AIST, Japan</i>
13:00 (5-1)	Laser Deposition for the Controlled Co-Deposition of Organolead Halide Perovskite T. Miyadera, T. Sugita, H. Tampo, K. Matsubara, M. Chikamatsu, <i>Nat'l Inst. of Advanced Industrial Sci. and Technol., Japan</i> 280
13:20 (5-2)	Internal Resistance of Perovskite Solar Cells under Low Illuminance Conditions I. Raifuku ¹ , Y. Ishikawa ¹ , S. Ito ² , Y. Uraoka ¹ , ¹ <i>Nara Inst. of Sci. and Technol., Japan</i> , ² <i>Univ. of Hyogo, Japan</i> 283

Session 6 : Advanced Processing and Devices (13 : 40 ~ 14 : 20)

Chairpersons :	Y. Wang, <i>Univ. of Maryland, USA</i> T. Matsuda, <i>Ryukoku Univ., Japan</i>
13:40 (6-1)	Surface Passivation of Crystalline Silicon by Heat Treatment in Liquid Water T. Motoki ¹ , K. Yasuta ¹ , H. Suzuki ¹ , T. Nakamura ¹ , M. Hasumi ¹ , T. Sameshima ¹ , T. Mizuno ² , ¹ <i>Tokyo Univ. of Agriculture and Technol., Japan</i> , ² <i>Kanagawa Univ., Japan</i> 286
14:00 (6-2)	Electroluminescence Emission Patterns of Organic Light-Emitting Transistors Based on Crystallized Fluorene-Type Polymers H. Kajii, T. Ohtomo, Y. Ohmori, <i>Osaka Univ., Japan</i> 290

— Coffee Break —

Session 7 : Basic Properties of Oxide TFTs (14 : 35 ~ 15 : 40)

Chairpersons : K. Ishida, *Technische Universitaet Dresden, Germany*
Y. Terai, *JOLED, Japan*

14:35 (7-1)	High Mobility SnO ₂ TFT for Display and Future IC (Invited) A. Chin ¹ , C. W. Shih ¹ , C. F. Lu ² , W. F. Su ² , ¹ <i>Nat'l Chiao Tung Univ., Taiwan</i> , ² <i>Nat'l Taiwan Univ., Taiwan</i>	294
15:00 (7-2)	Why High-Pressure Sputtering must be Avoided to Deposit a-In-Ga-Zn-O Films K. Ide, M. Kikuchi, M. Sasase, H. Hiramatsu, H. Kumomi, H. Hosono, T. Kamiya, <i>Tokyo Inst. of Technol., Japan</i>	298
15:20 (7-3)	Comparative Study on Light-Induced Negative-Bias Stress Stabilities in Amorphous In-Ga-Zn-O Thin Film Transistors with Photoinduced Transient Spectroscopy K. Hayashi, M. Ochi, A. Hino, H. Tao, H. Goto, T. Kugimiya, <i>Kobe Steel, Japan</i>	302

Closing Remarks (15 : 40 ~ 15 : 45)

Author Interviews (15 : 45 ~ 16 : 15)